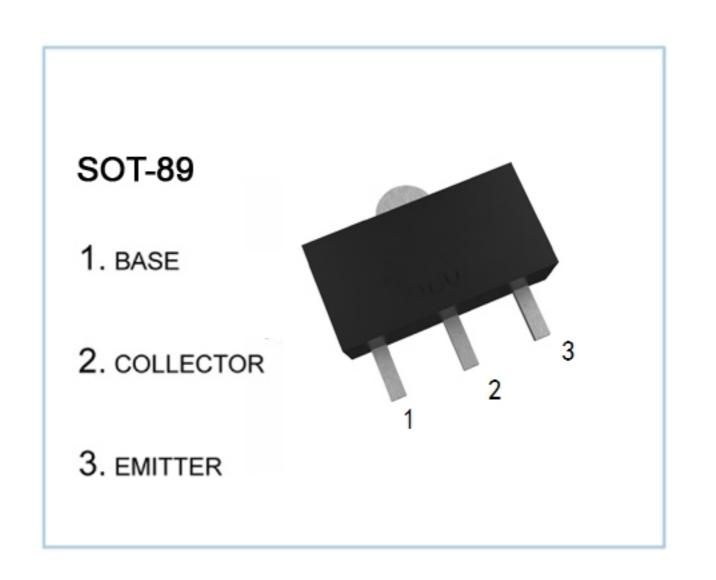


Features

- Low saturation voltage. VcE(sat)=-0.35V(Max.) at Ic / IB=-1A/-50mA.
- Excellent DC current gain characteristics.
- Complements the 2SA1797 and 2SC4672.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-emitter Voltage	VCEO	-50	V
Collector-base Voltage	Vсво	-50	V
Emitter-base Voltage	VEBO	-6	V
Collector current	Ic	-1.5	Α
Collector power dissipation	Pc	0.5	W
Jumction temperature	Tj	150	℃
Storage temperature	Tstg	-55 to +150	℃

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Тур	Max	Unit
Collector-emitter breakdown voltage	BVceo	Ic = -1mA	-50			٧
Collector-base breakdown voltae	ВУсво	Ic = -50 μ A	-50			V
Emitter-base breakdown voltage	ВУЕВО	IE = -50 μ A	-6			V
Collector cutoff current	Ісво	Vcb = -50V			-0.1	μΑ
Emitter cutoff current	ІЕВО	VEB = -5V			-0.1	μΑ
Collector-Emitter Saturation Voltage	VCE(sat)	Ic = -1A , IB = -50mA		-0.15	-0.35	V
DC current transfer ratio	hFE	Vce = -2V , Ic = -0.5A	82		390	
Transition frequency	fτ	Vce = -2V , Ie = 0.5A , f = 100MHz		200		MHz
Output Capacitance	Cob	Vcb = -10V , IE = 0A , f = 1MHz		36		pF

■ hFE Classification

Marking	AG			
Rank	Р	Q	R	
hFE	82~180	120~270	180~390	

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